WHAT IS CLAIMED IS:

- 1. An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing an ammonia gas and a fluorine gas as main constituents.
 - 2. The etching method of claim 1, wherein said etching gas contains an inert gas.
- 3. An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a hydrogen gas, a nitrogen gas, and a fluorine gas as main constituents.
 - 4. The etching method of claim 3, wherein said etching gas contains an inert gas.
- 5. An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a hydrogen gas and a nitrogen trifluoride gas as main constituents.
 - 6. The etching method of claim 5, wherein said etching gas contains an inert gas.
- 7. An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a nitrogen gas and a hydrogen fluoride gas as main constituents.
 - 8. The etching method of claim 7, wherein said etching gas contains an inert gas.

- 9. An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a nitrogen gas and a fluorinated hydrocarbon gas as main constituents.
 - 10. The etching method of claim 9, wherein said etching gas contains an inert gas.
- 11. An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon dioxide gas and a fluorine gas as main constituents.
- 12. The etching method of claim 11, wherein said etching gas contains an inert gas.
- 13. An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon dioxide gas and a fluorinated hydrocarbon gas as main constituents.
- 14. The etching method of claim 13, wherein said etching gas contains an inert gas.
- 15. An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon monoxide gas and a fluorine gas as main constituents.
- 16. The etching method of claim 15, wherein said etching gas contains an inert gas.

- 17. An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon monoxide gas and a fluorinated hydrocarbon gas as main constituents.
- 18. The etching method of claim 17, wherein said etching gas contains an inert gas.